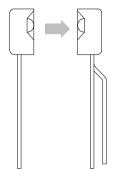
# **TCZS8100**

## **Matchable Pairs-Emitter and Detector**

## Description

Pairs of infrared emitting diode and photologic detector, matched in their optical and electrical features. These pairs enable a lot of applications. They can be used both for transmissive or reflective sensor functions. The peak wavelength of the emitter is  $\lambda = 950$  nm. The detector consists of a photologic IC with Schmitt-Trigger and open collector output.



#### Applications

- Detection of opaque material, documents etc
- Paper position sensor in copy machines
- Position sensor for shaft encoders

#### Handling precaution:

Connect a capacitor C of more than 100 nF between  $V_{S1}$  and Ground !

### Features

- Output level "low" when infrared beam is not interrupted
- TTL compatible
- Small dimensions

- Detector provided with optical filterEmitter and detector in side view case
- Miniature plastic case with lens
- Operating angle  $\pm \phi = 35^{\circ}$

## **Pin Connection**

## Absolute Maximum Ratings

#### **Input (Emitter)**

Parameters	Test Conditions	Symbol	Value	Unit
Reserve voltage		V <sub>R</sub>	6	V
Forward current		IF	60	mA
Forward surge current	$t_p \le 10 s$	I <sub>FSM</sub>	3	А
Power dissipation	$T_{amb} \le 25^{\circ}C$	P <sub>v</sub>	100	mW
Junction temperature		Ti	100	°C

#### **Output (Detector)**

Parameters	Test Conditions	Symbol	Value	Unit
Supply voltages		V <sub>S1</sub>	16	V
		V <sub>S2</sub>	20	V
Output current		Io	20	mA
Power dissipation	$T_{amb} \le 85^{\circ}C$	Pv	50	mW
Junction temperature		Ti	100	°C

#### **Emitter and Detector matched**

Parameters	Test Conditions	Symbol	Value	Unit
Ambient temperature range		T <sub>amb</sub>	-25 to +85	°C
Storage temperature range		T <sub>stg</sub>	-40 to +100	°C
Soldering temperature	2 mm from case, $t \le 5$ s	T <sub>sd</sub>	260	°C

## **Electrical Characteristics** $T_{amb} = 25^{\circ}C$

#### **Input (Emitter)**

Parameters	Test Conditions	Symbol	Min.	Тур.	Max.	Unit
Forward voltage	$I_F = 50 \text{ mA}$	V <sub>F</sub>		1.25	1.6	V
Breakdown voltage	$I_R = 100 \ \mu A$	V <sub>(BR)</sub>	6			V
Junction capacitance	$V_{R} = 0, f = 1 MHz$	Ci		50		pF

#### **Output (Detector)**

Parameters	Test Conditions	Symbol	Min.	Тур.	Max.	Unit
Supply voltage range		V <sub>S1</sub>	4.5		16	V

#### Emitter and Detector matched <sup>1)</sup>

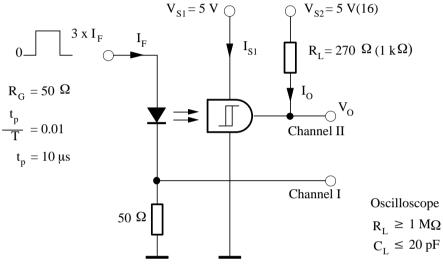
Parameters	Test Conditions	Symbol	Min.	Тур.	Max.	Unit
Supply current	$V_{S1} = 16 V$	I <sub>s1</sub>		3	5	mA
Output current	$V_{S1} = V_{S2} = 16 \text{ V},$ $I_F = 0$	I <sub>OH</sub>			1	μΑ
Input threshold current	$V_{S1} = 5 V$	I <sub>FT</sub>		3	10	mA
Hysteresis	$V_{S1} = 5 V$	I <sub>Foff</sub> /I <sub>Fon</sub>		80		%
Output voltage	$I_{OL} = 16 \text{ mA}, I_F > I_{FT}$ $V_{S1} = 5 \text{ V}$			0.15	0.4	V
Switching frequency	$I_F = 3 \text{ x } I_{FT}, R_L = 1 \text{ k}\Omega$ $V_{S1} = V_{S2} = 5 \text{ V}$	f <sub>sw</sub>		200		KHz

<sup>1)</sup> characteristics are measured at a separation distance of 4 mm (1.55") within a common axis of 0.5 mm (0.02") and parallel within  $5^{\circ}$ .

## **Switching Characteristics**

see test circuit

Parameters	Test Conditions	Symbol	Min.	Тур.	Max.	Unit
Rise time	$V_{S1} = V_{S2} = 5 V,$	t <sub>r</sub>		50		ns
Turn on time		t <sub>pHL</sub>		1		μs
Fall time	$I_F = 3 \times I_{FT},$ $R_L = 1 k\Omega$	t <sub>f</sub>		20		ns
Turn off time	KL = 1 KS2	t <sub>pLH</sub>		3		μs



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Figure 1. Test Circuit

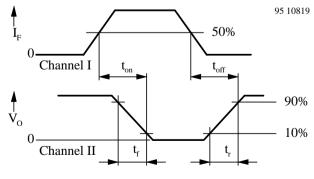


Figure 2. Pulse Diagram

# **TCZS8100**

## **Ozone Depleting Substances Policy Statement**

It is the policy of TEMIC TELEFUNKEN microelectronic GmbH to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

**TEMIC TELEFUNKEN microelectronic GmbH** semiconductor division has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

**TEMIC** can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use TEMIC products for any unintended or unauthorized application, the buyer shall indemnify TEMIC against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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